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# FCP36N60N / FCPF36N60NT

## N-Channel SupreMOS® MOSFET

600 V, 36 A, 90 mΩ

### Features

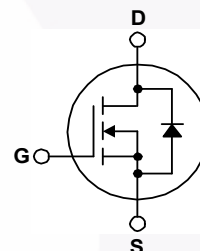
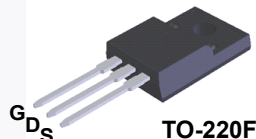
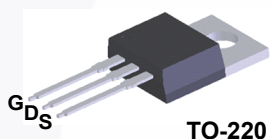
- $R_{DS(on)} = 81 \text{ m}\Omega$  (Typ.) @  $V_{GS} = 10 \text{ V}$ ,  $I_D = 18 \text{ A}$
- Ultra Low Gate Charge (Typ.  $Q_g = 86 \text{ nC}$ )
- Low Effective Output Capacitance (Typ.  $C_{oss(eff.)} = 361 \text{ pF}$ )
- 100% Avalanche Tested
- RoHS Compliant

### Application

- Solar Inverter
- AC-DC Power Supply

### Description

The SupreMOS® MOSFET is Fairchild Semiconductor's next generation of high voltage super-junction (SJ) technology employing a deep trench filling process that differentiates it from the conventional SJ MOSFETs. This advanced technology and precise process control provides lowest  $R_{sp}$  on-resistance, superior switching performance and ruggedness. SupreMOS MOSFET is suitable for high frequency switching power converter applications such as PFC, server/telecom power, FPD TV power, ATX power, and industrial power applications.



### Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	FCP36N60N	FCPF36N60NT	Unit
$V_{DSS}$	Drain to Source Voltage	600		V
$V_{GSS}$	Gate to Source Voltage	±30		V
$I_D$	Drain Current	- Continuous ( $T_C = 25^\circ\text{C}$ )	36	A
		- Continuous ( $T_C = 100^\circ\text{C}$ )	22.7	
$I_{DM}$	Drain Current	- Pulsed (Note 1)	108	A
$E_{AS}$	Single Pulsed Avalanche Energy	(Note 2)	1800	mJ
$I_{AR}$	Avalanche Current	(Note 1)	12	A
$E_{AR}$	Repetitive Avalanche Energy	(Note 1)	3.12	mJ
$dv/dt$	MOSFET $dv/dt$		100	V/ns
	Peak Diode Recovery $dv/dt$	(Note 3)	20	
$P_D$	Power Dissipation	( $T_C = 25^\circ\text{C}$ )	312	W
		- Derate Above $25^\circ\text{C}$	2.6	W/ $^\circ\text{C}$
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +150		$^\circ\text{C}$
$T_L$	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds	300		$^\circ\text{C}$

\*Drain current limited by maximum junction temperature.

### Thermal Characteristics

Symbol	Parameter	FCP36N60N	FCPF36N60NT	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.4	3.5	$^\circ\text{C/W}$
$R_{\theta CS}$	Thermal Resistance, Case to Heat Sink, Typ.	0.5	0.5	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	62.5	

## Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FCP36N60N	FCP36N60N	TO-220	Tube	N/A	N/A	50 units
FCPF36N60NT	FCPF36N60NT	TO-220F	Tube	N/A	N/A	50 units

## Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
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### Off Characteristics

$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = 1\text{ mA}$ , $V_{GS} = 0\text{ V}$ , $T_C = 25^\circ\text{C}$	600	-	-	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 1\text{ mA}$ , Referenced to $25^\circ\text{C}$	-	0.7	-	$V/^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 480\text{ V}$ , $V_{GS} = 0\text{ V}$	-	-	10	$\mu\text{A}$
		$V_{DS} = 480\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_C = 125^\circ\text{C}$	-	-	100	
$I_{GSS}$	Gate to Body Leakage Current	$V_{GS} = \pm 30\text{ V}$ , $V_{DS} = 0\text{ V}$	-	-	$\pm 100$	nA

### On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$ , $I_D = 250\text{ }\mu\text{A}$	2.0	-	4.0	V
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{ V}$ , $I_D = 18\text{ A}$	-	81	90	m $\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 20\text{ V}$ , $I_D = 18\text{ A}$	-	41	-	S

### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = 100\text{ V}$ , $V_{GS} = 0\text{ V}$ , $f = 1\text{ MHz}$	-	3595	4785	pF
$C_{oss}$	Output Capacitance		-	149	200	pF
$C_{rss}$	Reverse Transfer Capacitance		-	4	6	pF
$C_{oss}$	Output Capacitance	$V_{DS} = 380\text{ V}$ , $V_{GS} = 0\text{ V}$ , $f = 1\text{ MHz}$	-	80	-	pF
$C_{oss(eff.)}$	Effective Output Capacitance	$V_{DS} = 0\text{ V to } 380\text{ V}$ , $V_{GS} = 0\text{ V}$	-	361	-	pF
$Q_{g(tot)}$	Total Gate Charge at 10V	$V_{DS} = 380\text{ V}$ , $I_D = 18\text{ A}$ , $V_{GS} = 10\text{ V}$ (Note 4)	-	86	112	nC
$Q_{gs}$	Gate to Source Gate Charge		-	15.4	-	nC
$Q_{gd}$	Gate to Drain "Miller" Charge		-	26.4	-	nC
ESR	Equivalent Series Resistance	$f = 1\text{ MHz}$	-	1	-	$\Omega$

### Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 380\text{ V}$ , $I_D = 18\text{ A}$ , $V_{GS} = 10\text{ V}$ , $R_G = 4.7\text{ }\Omega$ (Note 4)	-	23	56	ns
$t_r$	Turn-On Rise Time		-	22	54	ns
$t_{d(off)}$	Turn-Off Delay Time		-	94	198	ns
$t_f$	Turn-Off Fall Time		-	4	18	ns

### Drain-Source Diode Characteristics

I <sub>S</sub>	Maximum Continuous Drain to Source Diode Forward Current	-	-	18	A	
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Forward Current	-	-	108	A	
V <sub>SD</sub>	Drain to Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 18 A	-	-	1.2	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 18 A, dI <sub>F</sub> /dt = 100 A/μs	-	574	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge		-	10	-	μC

#### Notes:

1. Repetitive rating: pulse-width limited by maximum junction temperature.
2.  $I_{AS} = 12\text{ A}$ ,  $R_G = 25\text{ }\Omega$ , starting  $T_J = 25^\circ\text{C}$ .
3.  $I_{SD} \leq 36\text{ A}$ ,  $di/dt \leq 200\text{ A}/\mu\text{s}$ ,  $V_{DD} = 380\text{ V}$ , starting  $T_J = 25^\circ\text{C}$ .
4. Essentially independent of operating temperature typical characteristics.

## Typical Performance Characteristics

Figure 1. On-Region Characteristics

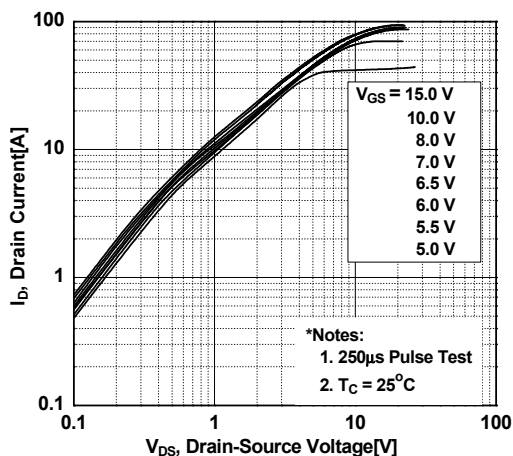


Figure 2. Transfer Characteristics

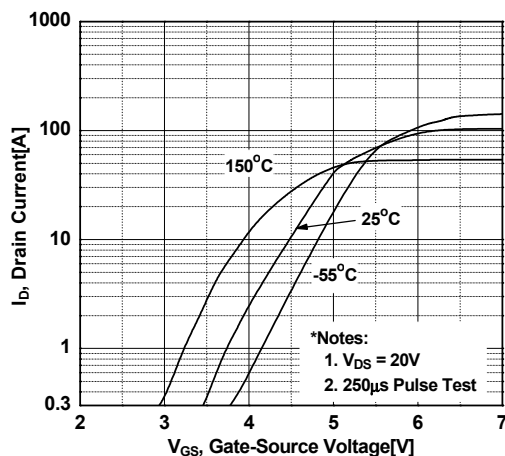


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

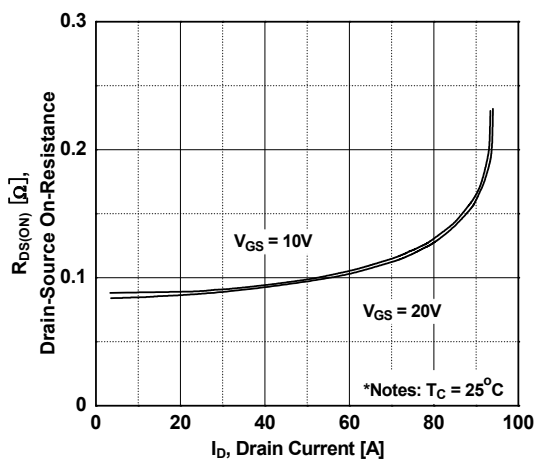


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

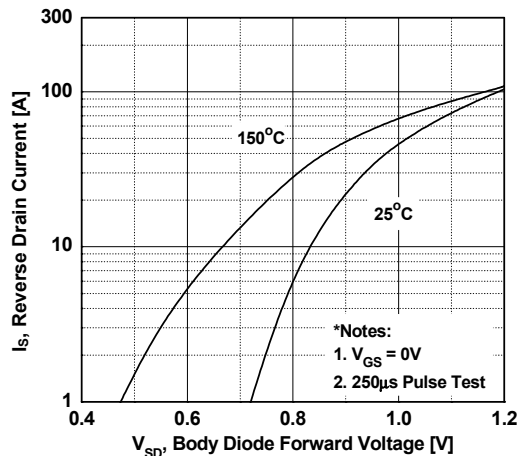


Figure 5. Capacitance Characteristics

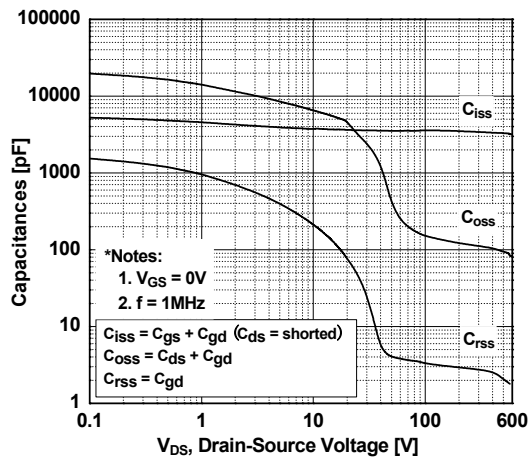
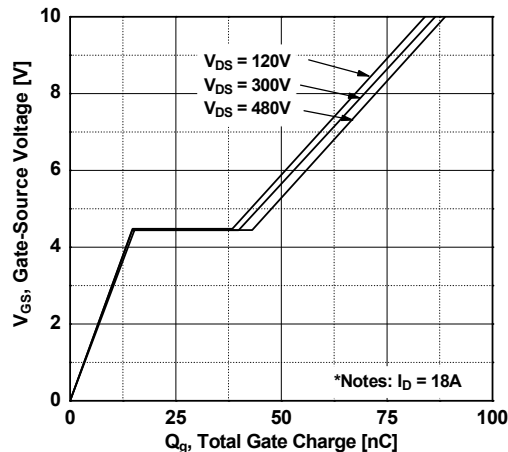
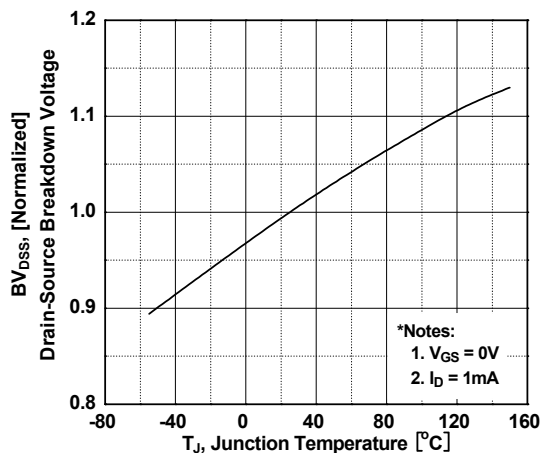


Figure 6. Gate Charge Characteristics

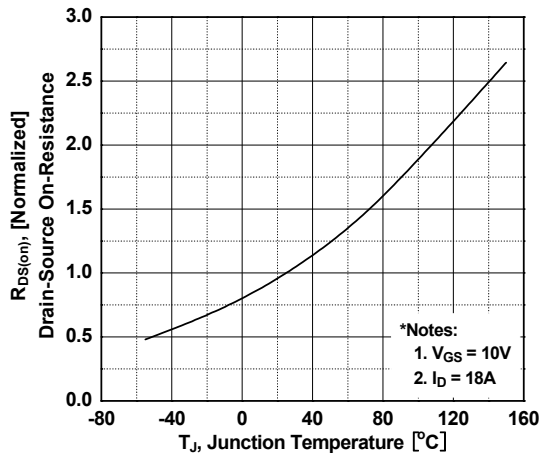


## Typical Performance Characteristics (Continued)

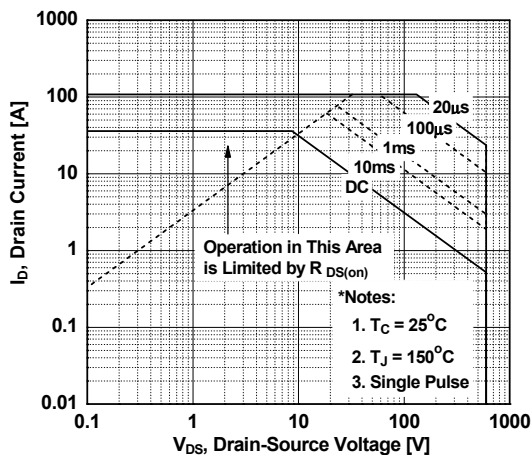
**Figure 7. Breakdown Voltage Variation vs. Temperature**



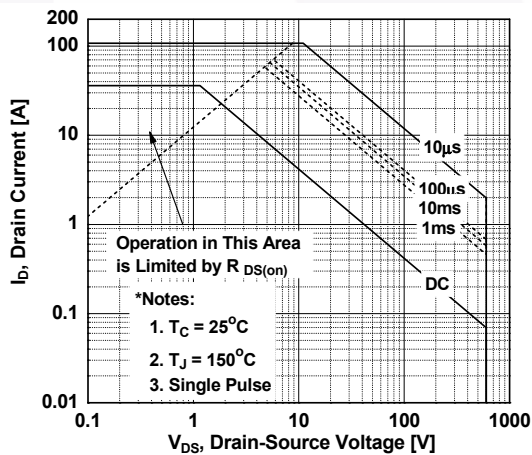
**Figure 8. On-Resistance Variation vs. Temperature**



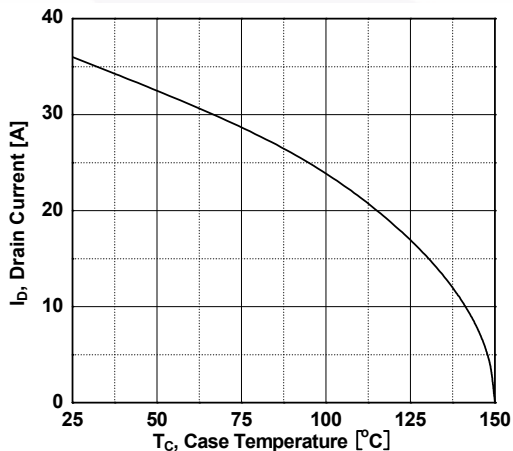
**Figure 9. Maximum Safe Operating Area for FCP36N60N**



**Figure 10. Maximum Safe Operating Area for FCPF36N60NT**



**Figure 11. Maximum Drain Current vs. Case Temperature**



## Typical Performance Characteristics (Continued)

Figure 12. Transient Thermal Response Curve for FCP36N60N

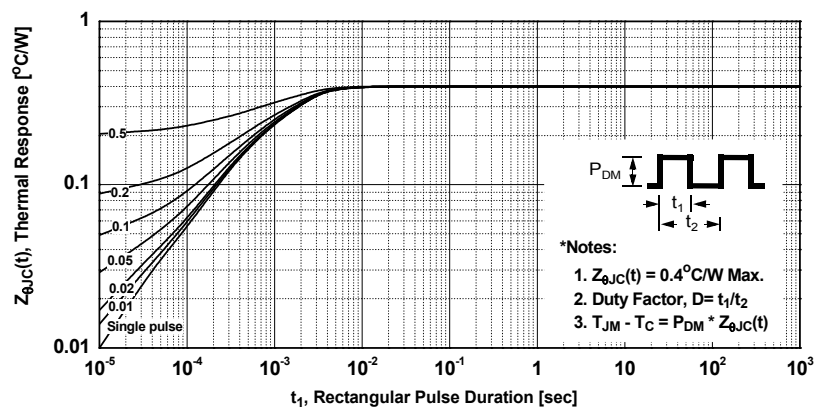


Figure 13. Transient Thermal Response Curve for FCPF36N60NT

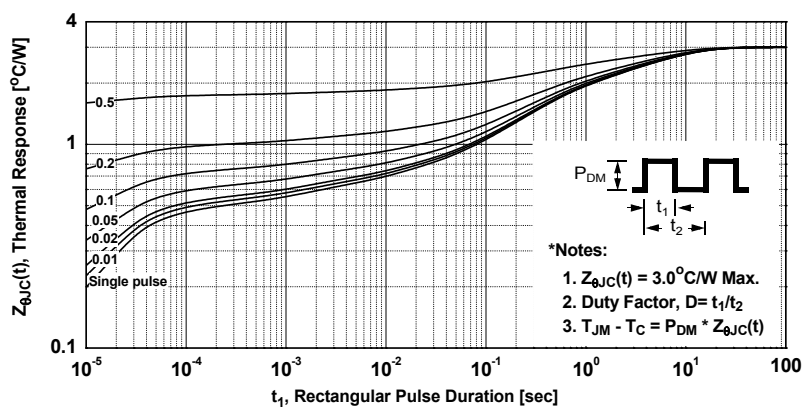




Figure 14. Gate Charge Test Circuit & Waveform

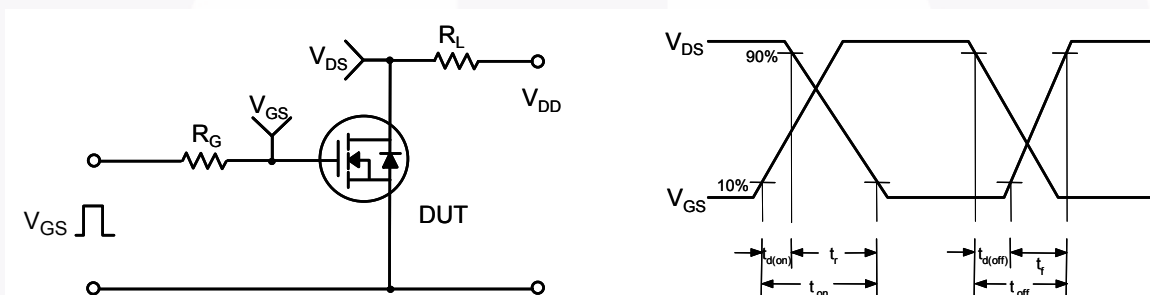


Figure 15. Resistive Switching Test Circuit & Waveforms

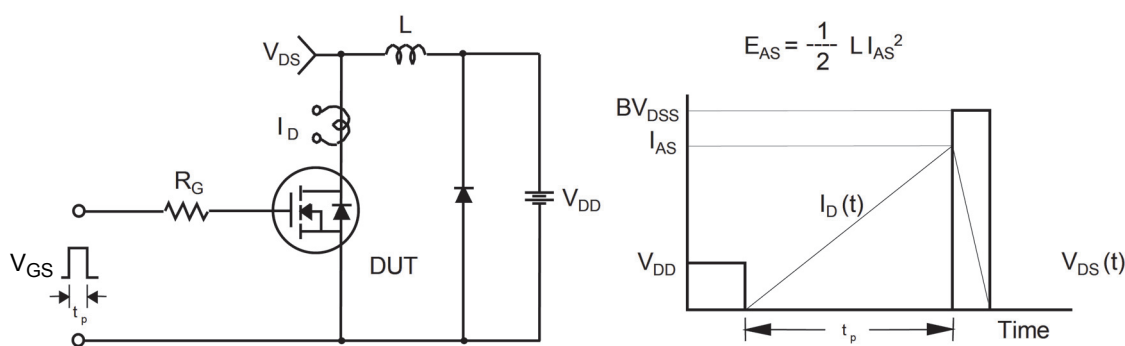


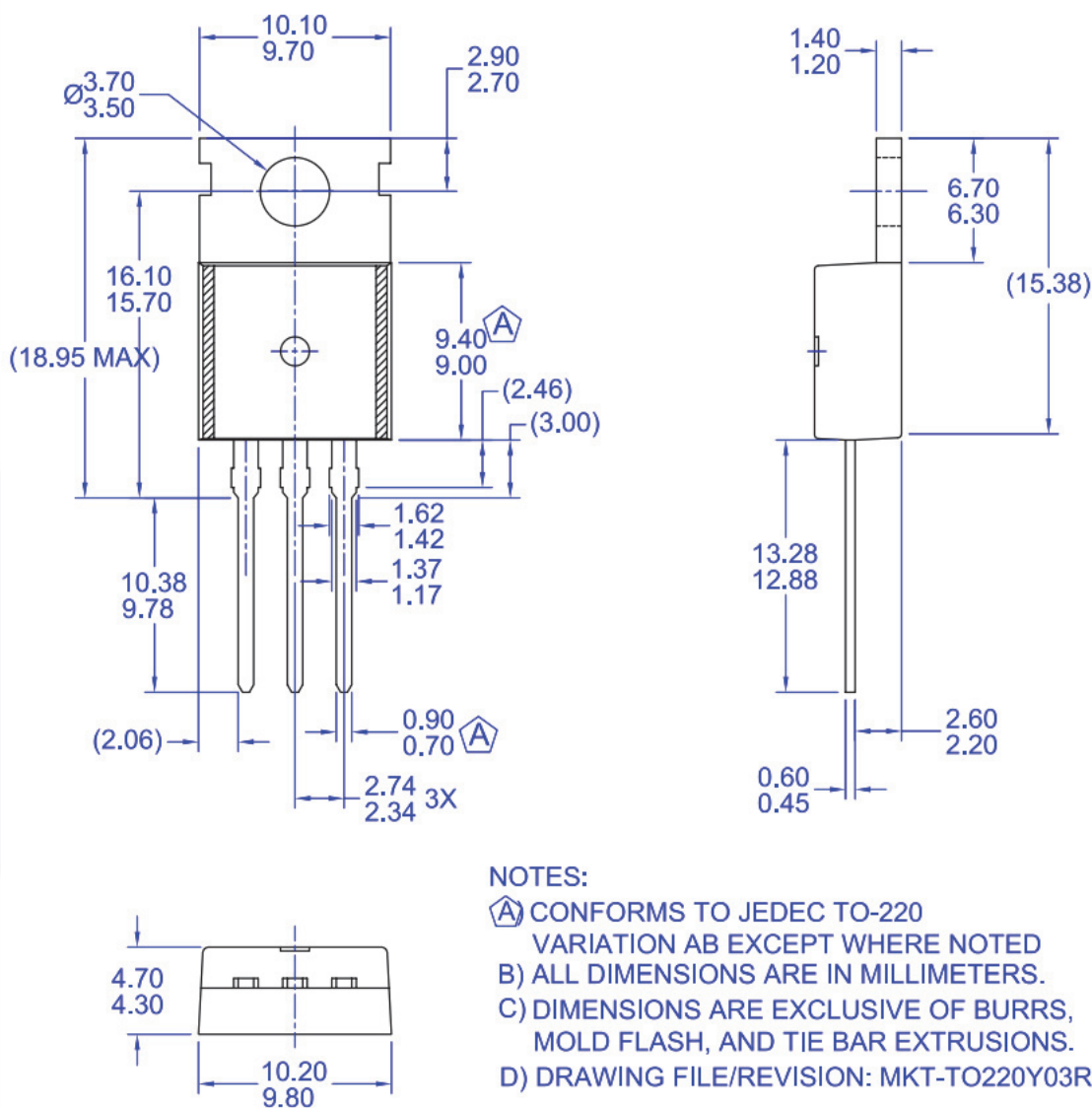
Figure 16. Unclamped Inductive Switching Test Circuit & Waveforms



Figure 17. Peak Diode Recovery  $dv/dt$  Test Circuit & Waveforms



## Mechanical Dimensions



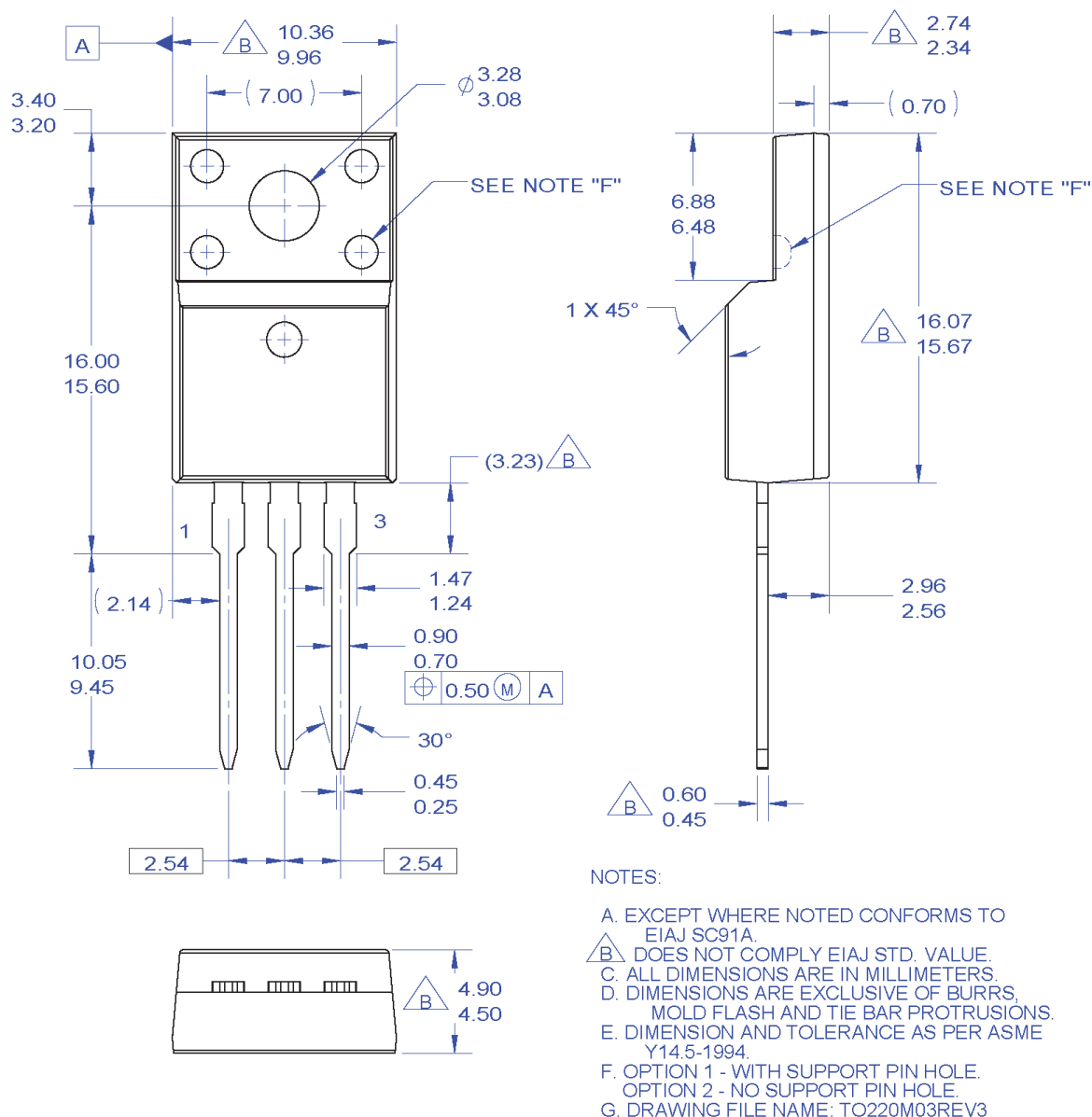
**Figure 18. TO220, Molded, 3-Lead, Non Jedec Variation AB**

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## Mechanical Dimensions



**Figure 19. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Straight Lead**

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